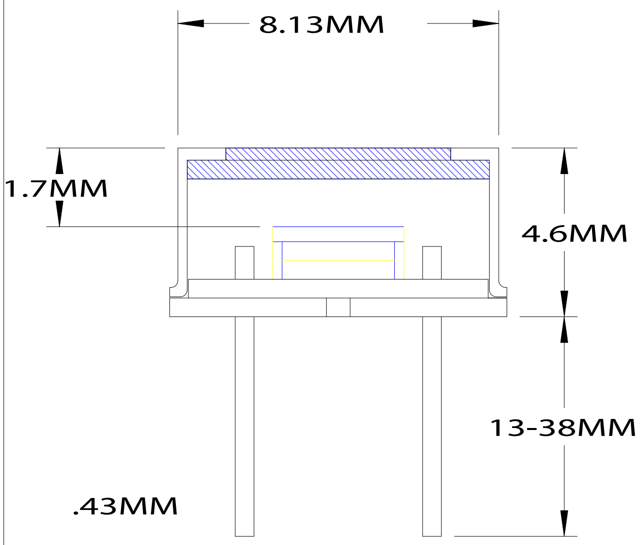


Si SPECIFICATIONS

TOP Si PV PHOTODIODE

ACTIVE AREA - 3.5MM Dia

WAVELENGTH - .3-1.1u

SHUNT RESISTANCE - 1500M @1OmV

DARK CURRENT - 0.2nA @10V

CAPACITANCE - 100pF @0V

RESPONSIVITY - .65A/W @900nm

NEP(W/Hz)-<1.3X10^{14} @900nm

TIME CONSTANT - 2000ns @0V

PbS SPECIFICATIONS

BOTTOM PbS PC DETECTOR

ACTIVE AREA - 3MMX3MM

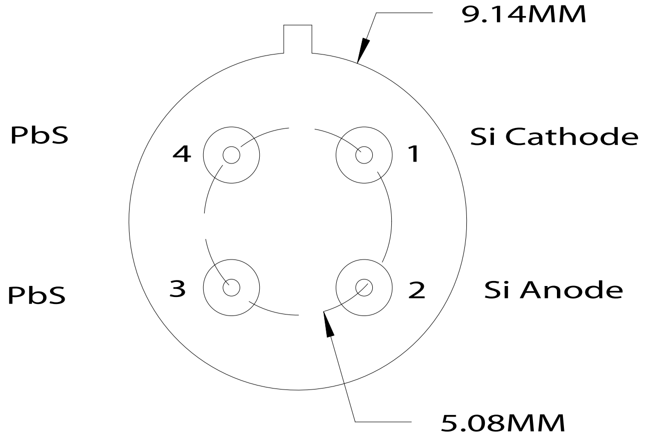
WAVELENGTH - 1.0 - 3.0u

RESISTANCE - 0.3 - 2.0 M ohms

RESPONSIVITY - >6X10^{4} V/W

D*(Pk,600,1)X10^{10}- 5.0 Min

TIME CONSTANT - 200-400usec



NOTE:

All assemblies are hermetically sealed

Custom filters are available

Other active areas are available

PbSe and InGaAs materials are available

DO NOT SCALE DRAWING	DRAWN		DATE
	CHECKED		DATE
	DESIGNER	GG	DATE
	ENGINEER	PB	DATE
MATERIAL:	PROJECT ENGINEER		DATE
	PROJECT APPROVAL PMB 3/3/09		DATE
FINISH SPECS:			

N.E.P.

NEW ENGLAND PHOTOCONDUCTOR

BS-2/2.5-5

SIZE A	CODE IDENT. NO.	TYPE	1643	REV
SCALE none			SHEET 1	